PDE Measurement of SiPMs

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Characterisation of SiPMs

- Test-setup for SiPM-measurements at KIP (Heidelberg)
 - Basic characterisation:
 - Dark-Rate
 - Crosstalk prob.
 - After-pulse prob.
 - Photon-Detection-Efficiency
 - Uniformity-Scans (Sensitivity, Gain, Crosstalk-Maps)

PDE Measurement Setup





- Power-ratio R (partial compensation of different sensitivities SiPM/Cal. Sensor)
- XE-Lamp + Monochromator (350-1000nm) Current-measurement (contains crosstalk and after-pulses)
 - relative PDE
- Pulsed laserdiodes/LEDs (465nm,633nm, 775nm, 870nm) QDC-readout (statistical analysis)
 - PDE without crosstalk and after-pulses

Measurement Principle

PDE without crosstalk and after-pulses

Photons, that arrive at the SiPM are Poisson-distributed:

$$P(n,\lambda) = \frac{\lambda^{n} \cdot e^{-\lambda}}{n!} \Rightarrow P(0,\lambda) = e^{-\lambda}$$
$$\Rightarrow \lambda = N_{pe} = -\ln\left(\frac{N_{Ped.}}{N_{Tot.}}\right)$$

N*_{Ped} is not influenced by optical crosstalk and afterpulses, but needs to be corrected for dark-rate:

$$N_{Ped}^* = N_{ped} - N_{dark}$$



Dark-rate Correction

The pedestal events N^{*}Ped. need to be corrected for the dark-rate. → Acquire dark-rate spectrum at each voltage value. Correction factor:

$$f = \frac{N_{>ped.}^{dark}}{N_{tot}^{dark}} = 1 - \frac{N_{ped}^{dark}}{N_{tot}^{dark}}$$
$$N_{Ped.} = \frac{N_{Ped.}^{*}}{1 - f}$$



Gain Measurement

• PDE as a function of $U_{over} = U_{bias} - U_{break}$

→ Calculate Ubreak (from linear fit results)



Automated Measurement (LABVIEW)

- I) Record photoelectron spectrum
- 2) Switch off light and record darkrate spectrum
- 3) Calculate gain and number of photoelectrons
- 4) Apply dark-rate correction \rightarrow PDE
- 5) Set new voltage
- 6) Start over at I

$$PDE = \frac{n_{pe}}{n_{ph}} = \frac{N_{pe} \cdot R/T}{P_{opt}/(h \cdot \frac{c}{\lambda})}$$

 $N_{pe} = Number of Photoelectrons/Pulse$

$$R = Power Ratio$$

$$T = Period \left(30 \cdot 10^{-6} s \right)$$

$$P_{opt} = Optical Power[W]$$

Example: PDE MPPC 1600pix.



Relative Measurement (350nm-1000nm)



PDE Measurement (Relative)



PDE Curve Scaling

- Curves are scaled to max.
 PDE value at 633nm
- Crosscheck: max. PDE-values at 465nm, 775nm and 870nm are shown.
 - Good agreement



PDE Curve SensL SPMICRO1020X13

- Scaled to max. PDE value at 633nm.
- Highest PDE at ~500nm
- steep curve below
 500nm





Wavelength [nm]

Uniformity Measurements

Setup for Uniformity-Scans



MPPC 10362-11-100C

 $U_{over} = I.IV$



40 Gain [QDC-Channels] y [mm] 0.8 30 0.6 20 0.4 10 0.2 0.8 0 0.2 0.40.6 1 x [mm]

Sensitivity and gain quite uniform.

Cross-talk probability strongly depends on position!

MPPC 10362-11-050C

U_{over}=1.3V



MPPC S10362-11-025C

U_{over}=2.3V



x [mm]



Conclusion

- <u>Setup for SiPM characterization established</u>
- Basic Characterisation
- Crosstalk and after-pulse measurements
- Temperature dependence
- Uniformity Scans (sensitivity, gain and crosstalk maps)
- PDE-measurement over wide spectral range (350-1000nm)

Backup Slides

PDE MPPC³⁰⁰ 600 Pixels 200 70 70.5 71 71.5 72 **Bias Voltage [V]**

350

- In the case of the MPPC with 1600 pixels the dark-rate correction is small (low dark-rate, short gate 50ns)
- In the following only corrected values are shown



72.5

Measurement of Power-ratio R (Ø=0.6mm aperture)



PDE (465nm, 633nm, 775nm, 870nm)

2

1

0

25



0.5 1.5 2.5 Overvoltage U s-U_{break} [V] ι ιαιτισαι δ **MICABILICI**

+ I

1.6 1.8 2 2.2 Overvoltage U_{bias}-U_{break} [V]

848 pix.

1 ¹ 1 ¹ 1

SiPM Positioning

- All light should hit the active SiPM-Surface.
- Ø=0.6mm aperture was used for measurements with pulsed laserdiodes.
- Plateau on top allows reproducible positioning at maximum.





Alexander Tadday, 22.02.2010, SiPM Workshop DESY Hamburg

Setup for Uniformity-Scans



Scan Sensor with pulsed lightspot (10000 pulses per meas. point) Versatile Analysis:

- Sensitivity Map N_{pe}(x,y)
- Gain Map G(x,y)
- Crosstalk Map C(x,y)

